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MITSUBISHI SEMICONDUCTOR <GaAs FET>

## MGFK39V4045

#### 14.0-14.5GHz BAND 8W INTERNALLY MATCHED GaAs FET

#### **DESCRIPTION**

The MGFK39V4045 is an internally impedance matched GaAs power FET especially designed for use in 14.0-14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

Internally impedance matched

Flip-chip mounted

High output power

P1dB = 8W(TYP.) @f=14.0-14.5GHz

High linear power gain

GLP = 5.5dB(TYP.) @f=14.0-14.5GHz

High power added efficiency

P.A.E. = 20% (TYP.) @f=14.0-14.5GHz

#### **APPLICATION**

For use in 14.0-14.5GHz band amplifiers

### **QUALITY GRADE**

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#### RECOMMENDED BIAS CONDITIONS

VDS =10 (V) ID =2.4 (A)

Refer to Bias Procedure

#### ABSOLUTE MAXIMUM RATINGS

(Ta=25de	g	C

Symbol	Parameter	Parameter Ratings					
VGDO	Gate to drain voltage	-15	V				
VGSO	Gate to source voltage	-15	V				
ID	Drain current	6	Α				
IGR	Reverse gate current	-18	mA				
IGF	Forward gate current	36	mA				
PT *1	Total power dissipation	42.8	W				
Tch	Channel temperature	175	deg.C				
Tstg	Storage temperature	-65 / +175	deg.C				
*1 : Tc=25dog C							

<sup>\*1 :</sup> Tc=25deg.C

### ELECTRICAL CHARACTERISTICS (Ta=25deg.C)

OUTLINE DRAWING Unit : millimeters
21.0+/03 (1) 06+/0.15 (2) (2) (3)
10.7 17.0 +/0.2
700+97 120
(1) GATE (2) SOURCE (FLANGE) (3) DRAIN

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Symbol	Parameter	Test conditions	Limits		Unit	
-			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VG=0V	ı	4	6	Α
gm	Transconductance	VDS=3V,ID=2.4A	1.2	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression		38.5	39	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=2.4A, f=14.0 - 14.5GHz	4.5	5.5	-	dB
P.A.E.	Power added efficiency		ı	20	-	%
Rth (Ch-C)	Thermal resistance *1	Delta Vf method	ı	-	3.5	deg.C/W

<sup>\*1 :</sup> Channel to case



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